AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-20 (Cancelled)

21. (Currently Amended) An integrated circuit, comprising:

an NFET having a gate electrode comprising a TiN layer superjacent a first gate dielectric, a first metal layer having laterally opposed vertical sidewalls, superjacent the TiN layer, wherein the TiN layer is adjacent to laterally opposed vertical sidewalls of the first metal layer; and

a PFET having a gate electrode comprising a TaN layer superjacent a second gate dielectric, a second metal layer having laterally opposed vertical sidewalls, superjacent the TaN layer, wherein the TaN layer is adjacent to laterally opposed vertical sidewalls of the second [[meta]] metal layer.

22. (Previously Presented) The integrated circuit of claim 21, wherein the first metal layer comprises one selected from the group consisting of aluminum, titanium, or a combination thereof.

23. (Currently Amended) The integrated circuit of claim 21, wherein the second metal layer comprises [[are]] one selected from the group consisting of nickel, platinum, palladium, or a combination thereof.

24. (Previously Presented) An microelectronic device, comprising:

an NFET having a first gate electrode comprising a TiN layer superjacent a first gate dielectric and adjacent to at least a pair of sidewall spacers, the TiN layer forming a lining over interior walls of the sidewall spacers and over the gate dielectric; and

a PFET having a second gate electrode comprising a TaN layer superjacent a second gate dielectric and adjacent to at least a second pair of sidewall spacers, the TaN layer forming a lining over interior walls of the second pair of sidewall spacers and over the second gate dielectric;

wherein the first gate electrode comprises aluminum and the second gate electrode comprises a material selected from the group consisting of Ni, Pt, Pd, and a combination thereof.

25. (Currently Amended) An integrated circuit, comprising:

a first FET of a first conductivity type, the first FET having a first work function modulation layer; and

a second FET of a second conductivity type[[;]], the second FET having a second work function modulation layer;

wherein the first and the second work function modulation layers comprise the same material, and wherein a thickness of the first work function modulation layer is different than a thickness of the second work function modulation layer.

26. (Previously Presented) The integrated circuit of claim 25, wherein the first and the second FETs have substantially identical channel doping profiles, and wherein the first and the second FETs have different threshold voltages.

27. (Previously Presented) A metal gate electrode comprising:

a gate dielectric layer;

spacers along laterally opposed sides of the gate dielectric layer;

a metal nitride layer superjacent the gate dielectric layer, the metal nitride layer having a first work function; and

a metal layer superjacent the metal nitride layer, the metal layer thicker than the metal nitride layer, the metal layer having a second work function and not being formed from a metal nitride.

28. (Previously Presented) The metal gate electrode of claim 27, wherein the metal nitride layer comprises a metal nitride selected from the group consisting of titanium nitride and tantalum nitride.

29. (Previously Presented) The metal gate electrode of claim 27, wherein the metal layer comprises a metal selected from the group consisting of aluminum, nickel, platinum and palladium.

30. (Previously Presented) The metal gate electrode of claim 29, wherein the metal nitride layer is less than 100 angstroms thick.

31. (Previously Presented) The metal gate electrode of claim 27, wherein the metal nitride layer comprises a work function modulation layer, a thickness of which is selected to achieve a particular work function.

32. (Previously Presented) The metal gate electrode of claim 27, wherein the metal nitride layer is selected from a material that provides a diffusion barrier from the metal layer to the gate dielectric.

33. (Currently Amended) A metal gate electrode comprising:

a gate dielectric layer;

spacers along laterally opposed sides of the gate dielectric layer;

a metal work function modulation layer superjacent the gate dielectric layer, the metal work function modulation layer having a thickness selected to achieve a particular work function for the gate electrode; and

a metal layer superjacent the metal work function modulation layer.

34. (Previously Presented) The metal gate electrode of claim 33, wherein the metal work function modulation layer comprises a metal nitride.

35. (Previously Presented) The metal gate electrode of claim 33, wherein the work function of the metal gate electrode is different from a work function of the metal work function modulation layer and a work function of the metal layer.

36. (Previously Presented) The metal gate electrode of claim 33, wherein the metal work function modulation layer has a thickness that is selected to achieve a threshold voltage.

37. (Currently Amended) The metal gate electrode of claim 33, wherein the metal work function modulation layer is selected from a material that provides a diffusion barrier from the metal layer to the gate dielectric layer.